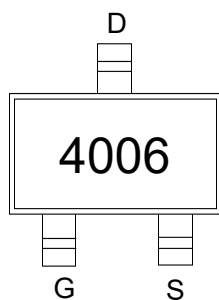


Features

- Trench Power LV MOSFET technology
- High density cell design for low $R_{DS(ON)}$
- High Speed switching

Application

- Battery protection
- Load switch
- Power management

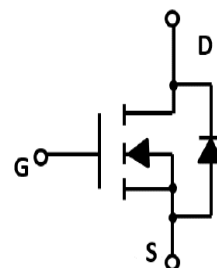
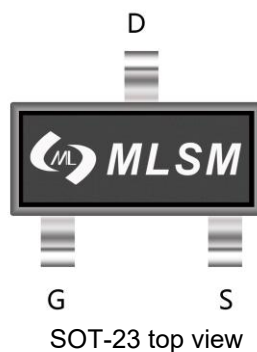


4006: Device code

Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
40V	30mΩ@10V	6A
	38mΩ@4.5V	



Schematic diagram



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_c=25^\circ\text{C}$ 6	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_c=25^\circ\text{C}$ 25	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$ 6	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$ 1.4	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	125	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS4006	SOT-23	4006	3,000	45,000	180,000	7"reel

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250μA	40	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=40V, VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.0	--	2.5	V
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=5.6A	--	30	40	mΩ
		VGS=4.5V, ID=4.5A	--	38	50	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
Ciss	Input Capacitance	VDS=20V, VGS=0V, f=1MHz	--	490	--	pF
Coss	Output Capacitance		--	92	--	pF
CRSS	Reverse Transfer Capacitance		--	68	--	pF
Switching Characteristics						
Qg	Total Gate Charge	VDS=20V, ID=3.5A, VGS=10V	--	5.2	--	nC
Qgs	Gate Source Charge		--	0.9	--	nC
Qgd	Gate Drain Charge		--	1.3	--	nC
td(on)	Turn-on Delay Time	VDD=20V, ID=3.8A, VGS=10V, RG=3Ω	--	13	--	nS
tr	Turn-on Rise Time		--	52	--	nS
td(off)	Turn-Off Delay Time		--	17	--	nS
tf	Turn-Off Fall Time		--	10	--	nS
Source- Drain Diode Characteristics						
VSD	Forward on voltage	TJ=25°C, IS=6A	--	--	1.2	V

Typical Operating Characteristics

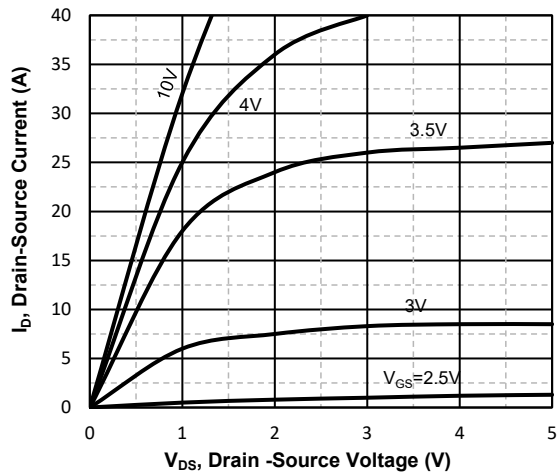


Fig1. Typical Output Characteristics

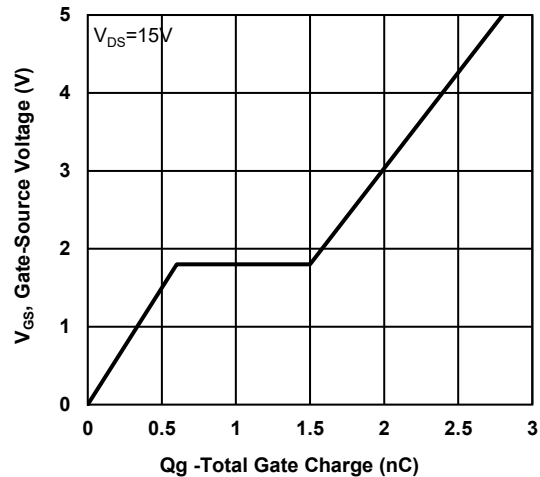


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

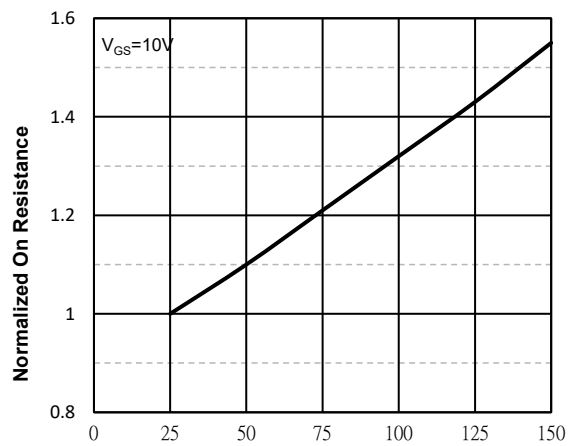


Fig3. Normalized On-Resistance Vs. Temperature

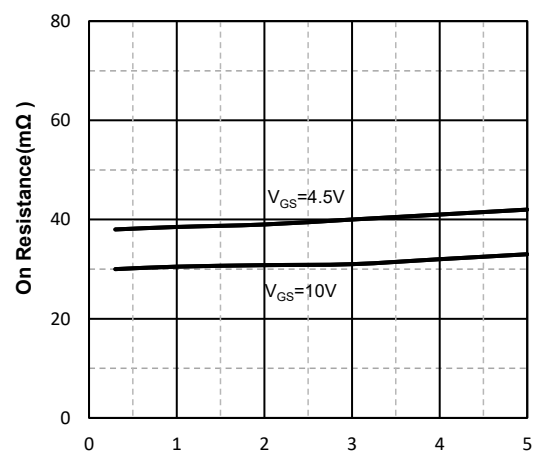


Fig4. On-Resistance Vs. Drain-Source

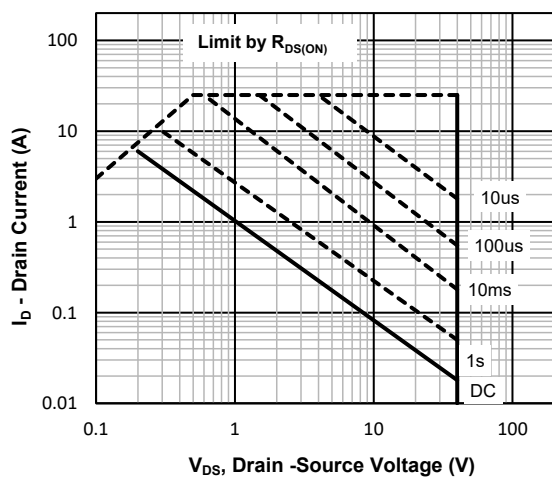


Fig5. Maximum Safe Operating Area

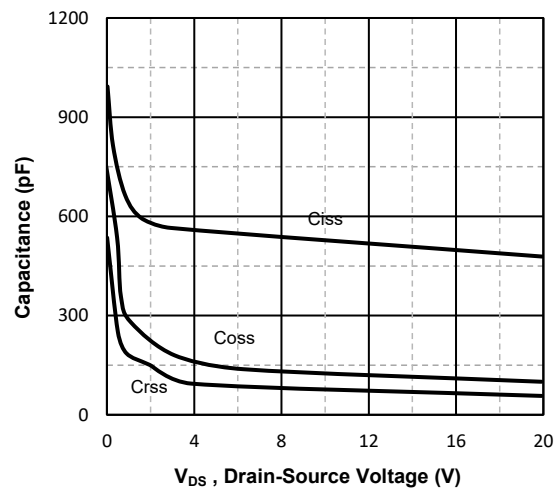
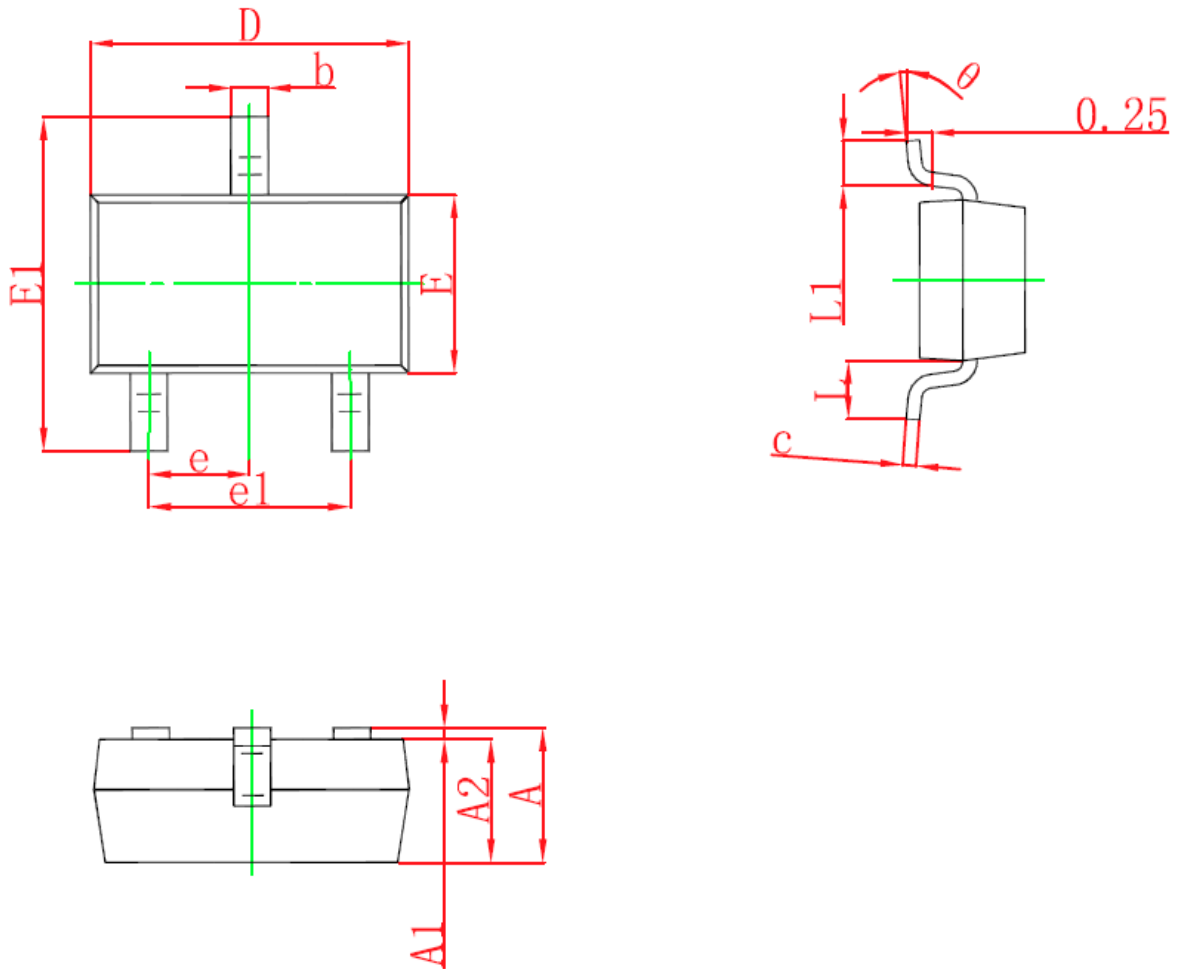


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-23 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E1	2.250	2.550	0.088	0.100
E	1.200	1.400	0.047	0.055
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°